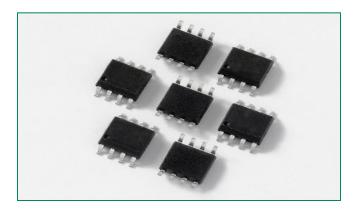
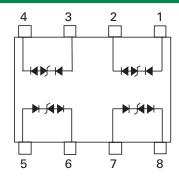
GREEN SPLV2.8-4 Lead-Free/Green Series HF RoHS



Description

The SPLV2.8-4 was designed to protect low voltage, CMOS devices from ESD and lightning induced transients. There is a compensating diode in series with each low voltage TVS to present a low loading capacitance to the line being protected. These robust structures can safely absorb repetitive ESD strikes at ±30kV (contact discharge) per IEC61000-4-2 standard and each structure can safely dissipate up to 24A (IEC61000-4-5, $t_p=8/20\mu s$) with very low clamping voltages.

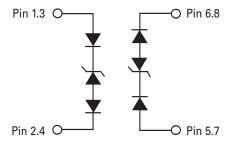
Pinout



Features

- ESD, IEC61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC61000-4-4, 40A (5/50ns)
- Lightning, IEC61000-4-5, 24A (8/20µs)
- Low capacitance of 3.8pF per line
- Low leakage current of 1µA (MAX) at 2.8V
- SOIC-8 pin configuration allows for simple flowthrough layout

Functional Block Diagram



Applications

- 10/100/1000 Ethernet
- WAN/LAN Equipment
- Switching Systems
- Desktops, Servers, and Notebooks
- Analog Inputs
- Base Stations

SPA™ Silicon Protection Array Products





Absolute Maximum Ratings

Parameter	Rating	Units
Peak Pulse Power (t _p =8/20µs)	400	W
Peak Pulse Current (t _p =8/20µs)	24	А
Operating Temperature	-40 to 85	°C
Storage Temperature	-60 to 150	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Characteristics (T_{OP} = 25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤1μA			2.8	V
Reverse Breakdown Voltage	V _{BR}	I _τ =2μA	3.0			V
Snap Back Voltage	V _{SB}	I _T =50mA	2.8			V
Reverse Leakage Current	LEAK	V _R =2.8V (Each Line)			1	μΑ
Clamping Voltage ¹	V _C	I _{PP} =5A, t _P =8/20μs (Each Line)		6.8	8.5	V
Clamping Voltage ¹	V _C	I _{pp} =24A, t _p =8/20μs (Each Line)		12.5	15.0	V
ESD Withstand Voltage ¹		IEC61000-4-2 (Contact)	±30			kV
	V _{ESD}	IEC61000-4-2 (Air)	±30			kV
Dynamic Resistance	R _{DYN}	(V _{C2} - V _{C1}) / (I _{PP2} - I _{PP1}) (Each Line)		0.3		Ω
Diode Capacitance ¹	C _D	V _R =0V, f=1MHz (Each Line)		3.8	5	pF

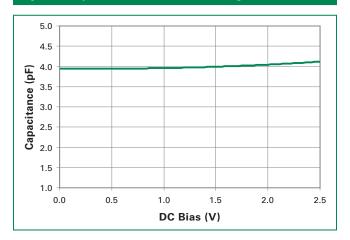
NOTES:

Revised: March 17, 2010

¹Parameter is guaranteed by design and/or device characterization.



Figure 1: Capacitance vs. Reverse Voltage



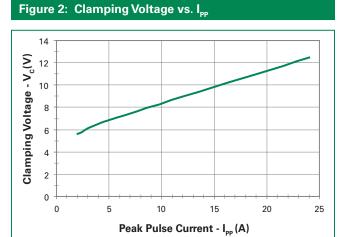
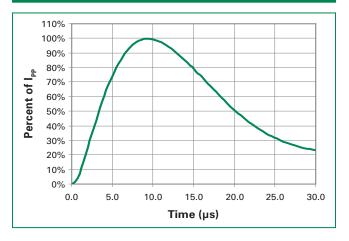


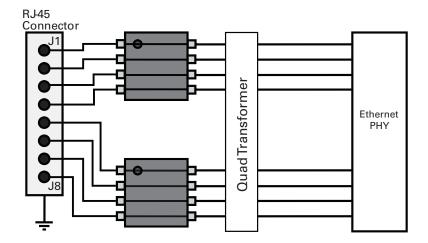
Figure 3: Pulse Waveform



Low Voltage, Diode Compensated TVS Array for ESD and Lightning Protection

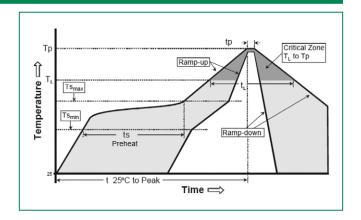


Application Example

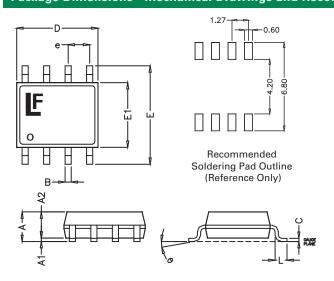


Soldering Parameters

Reflow Condition		Pb – Free assembly	
	-Temperature Min (T _{s(min)})	150°C	
Pre Heat	-Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 – 180 secs	
Average ramp up rate (Liquidus) Temp (T_L) to peak		5°C/second max	
T _{S(max)} to T _L - Ramp-up Rate		5°C/second max	
Reflow	-Temperature (T _L) (Liquidus)	217°C	
nellow	-Temperature (t _L)	60 – 150 seconds	
Peak Temperature (T _p)		250 ^{+0/-5} °C	
Time within 5°C of actual peak Temperature (t _p)		20 – 40 seconds	
Ramp-down Rate		5°C/second max	
Time 25°C to peakTemperature (T _P)		8 minutes Max.	
Do not exceed		260°C	

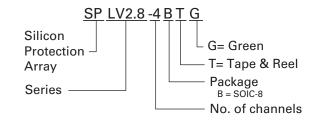


Package Dimensions - Mechanical Drawings and Recommended Solder Pad Outline



Package	MS-012 (SO-8)				
Pins	8				
JEDEC	MO-223 Issue A				
	Millin	netres	Inches		
	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A1	0.10	0.25	0.004	0.010	
A2	1.25	1.65	0.050	0.065	
В	0.31	0.51	0.012	0.020	
С	0.17	0.25	0.007	0.010	
D	4.80	5.00	0.189	0.197	
Е	5.80	6.20	0.228	0.244	
E1	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
L	0.40	1.27	0.016 0.050		

Part Numbering System



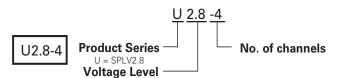
Product Characteristics

Lead Plating	Matte Tin
Lead Material	Copper Alloy
Lead Coplanarity	0.0004 inches (0.102mm)
Subsitute Material	Silicon
Body Material	Molded Epoxy
Flammability	UL94-V-0

Notes :

- All dimensions are in millimeters
- 2. Dimensions include solder plating.
- 3. Dimensions are exclusive of mold flash & metal burr.
- 4. All specifications comply to JEDEC SPEC MO-203 Issue A
- 5. Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
- 6. Package surface matte finish VDI 11-13.

Part Marking System



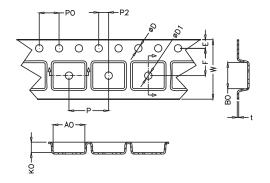
Ordering Information

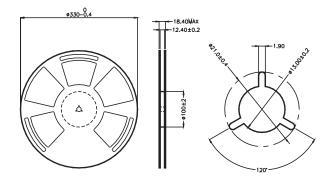
Part Number	Package	Marking	Min. Order Qty.
SPLV2.8-4BTG	SOIC-8	U2.8-4	2500





Embossed Carrier Tape & Reel Specification - SOIC Package





Cyma b a l	Millimetres		Inches		
Symbol	Min	Max	Min	Max	
E	1.65	1.85	0.065	0.073	
F	5.4	5.6	0.213	0.22	
P2	1.95	2.05	0.077	0.081	
D	1.5	1.6	0.059	0.063	
D1	1.50 Min		0.059 Min		
P0	3.9	4.1	0.154	0.161	
10P0	40.0 +/- 0.20		1.574 +/- 0.008		
W	11.9	12.1	0.468	0.476	
Р	7.9	8.1	0.311	0.319	
A0	6.3	6.5	0.248	0.256	
В0	5.1	5.3	0.2	0.209	
K0	2	2.2	0.079	0.087	
t	0.30 +/- 0.05		0.012 +/- 0.002		